

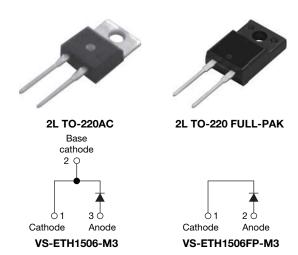
Vishay Semiconductors

COMPLIANT

HALOGEN

FREE

## Hyperfast Rectifier, 15 A FRED Pt®



PRODUCT SUMMARY					
Package	2L TO-220AC, 2L TO-220FP				
I <sub>F(AV)</sub>	15 A				
$V_{R}$	600 V				
V <sub>F</sub> at I <sub>F</sub>	2.45 V				
t <sub>rr</sub> (typ.)	21 ns				
T <sub>J</sub> max.	175 °C				
Diode variation	Single die				

#### **FEATURES**

- · Hyperfast soft recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- True 2 pin package
- Compliant to RoHS Directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition
- Designed and qualified according to JEDEC-JESD47



Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	$V_{RRM}$		600	V		
Average rectified forward current in DC —	I <sub>F(AV)</sub>	T <sub>C</sub> = 149 °C	15	А		
FULL-PAK		T <sub>C</sub> = 94 °C	15			
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	160			
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MAX. UI					
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 15 A	-	1.8	2.45	45 V	
Forward voltage		I <sub>F</sub> = 15 A, T <sub>J</sub> = 150 °C	-	1.25	1.6		
Doverno lockogo overnost		V <sub>R</sub> = V <sub>R</sub> rated	-	0.01	15		
Reverse leakage current I <sub>R</sub>		T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	20	200	μA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	12	=	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH	

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## VS-ETH1506-M3, VS-ETH1506FP-M3

# Vishay Semiconductors Hyperfast Rectifier, 15 A FRED Pt®



<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 A, dI_F/dt = 10$	$I_F = 1 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		21	26	
Poverse receivery time		$I_F = 15 \text{ A, } dI_F/dt = 100$	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		25	36	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	29	-	ns
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 15 A dI <sub>F</sub> /dt = 200 A/μs V <sub>B</sub> = 390 V	-	65	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	3.9	-	А
Peak recovery current		T 105 °C		-	7.0	-	A
Develope we develop a blown		T <sub>J</sub> = 25 °C		-	60	-	5
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	240	-	nC
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 15 A	-	42	-	ns
Peak recovery current	I <sub>RRM</sub>		T <sub>J</sub> = 125 °C	$dI_F/dt = 800 A/\mu s$	-	21	-
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	=	480	-	nC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C	
Thermal resistance,	В		-	1.2	1.4		
junction to case FULL-PAK	$R_{thJC}$		-	3.7	4.3		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W	
Typical thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-		
Maight			-	2	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6	_	12	kgf · cm	
Woulding torque			(5)	_	(10)	(lbf · in)	
Marking device		Case style 2L TO-220AC	POAC ETH1506		1506		
iviai kii ig device		Case style 2L TO-220 FULL-PAK		ETH1	506FP	•	



## Hyperfast Rectifier, 15 A FRED Pt® Vishay Semiconductors

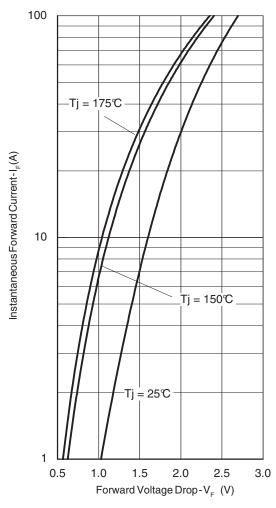


Fig. 1 - Typical Forward Voltage Drop Characteristics

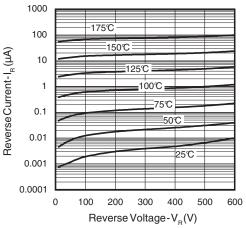


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

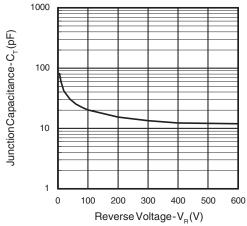


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

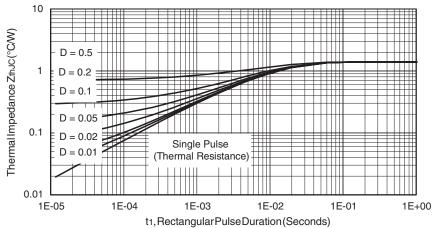


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

# Vishay Semiconductors Hyperfast Rectifier, 15 A FRED Pt®



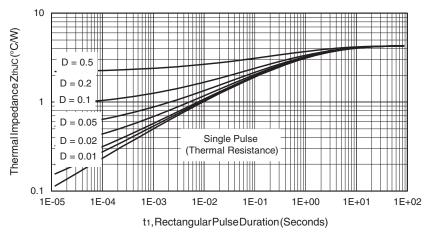


Fig. 5 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics (FULL-PAK)

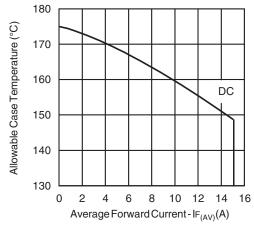


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

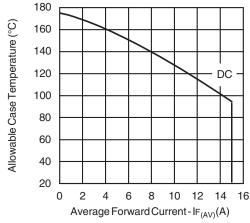


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

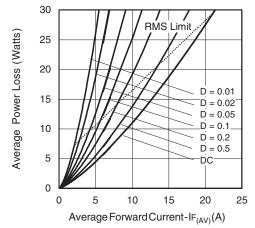


Fig. 8 - Forward Power Loss Characteristics





## Hyperfast Rectifier, 15 A FRED Pt® Vishay Semiconductors

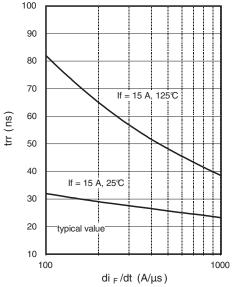


Fig. 9 - Typical Reverse Recovery vs. dl<sub>F</sub>/dt

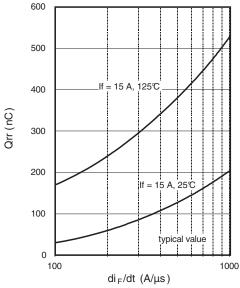


Fig. 10 - Typical Stored Charge vs. dl<sub>F</sub>/dt

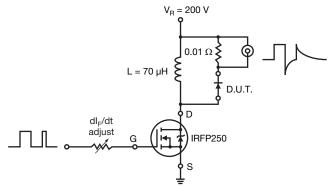
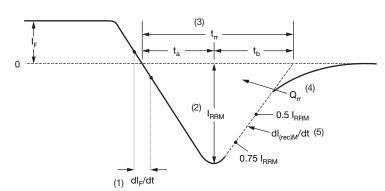


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $t_{rr}$  reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q<sub>rr</sub> area under curve defined by t<sub>rr</sub> and I<sub>RRM</sub>

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 12 - Reverse Recovery Waveform and Definitions

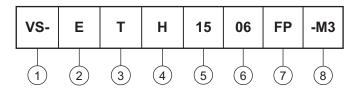
## VS-ETH1506-M3, VS-ETH1506FP-M3

Vishay Semiconductors Hyperfast Rectifier, 15 A FRED Pt®



#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Circuit configuration:

E = Single diode

**3** - T = TO-220

H = Hyperfast recovery time

5 - Current code: 15 = 15 A

Voltage code: 06 = 600 V

7 - • None = TO-220

• FP = FULL-PAK

8 - Environmental digit:

-M3 = Halogen-free, RoHS compliant and terminations lead (Pb)-free

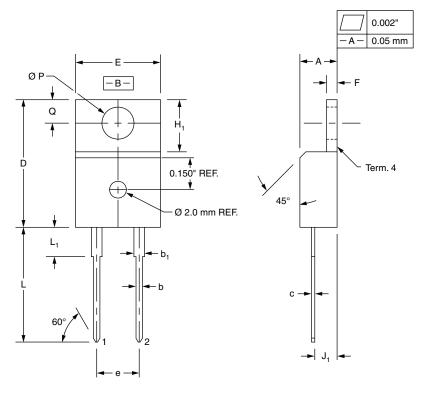
ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-ETH1506-M3	50	1000	Antistatic plastic tube			
VS-ETH1506FP-M3	50	1000	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS				
Dimensions	2L TO-220AC	www.vishay.com/doc?95259		
Dimensions	2L TO-220 FULL-PAK	www.vishay.com/doc?95260		
Part marking information	2L TO-220AC	www.vishay.com/doc?95391		
	2L TO-220 FULL-PAK	www.vishay.com/doc?95392		

Vishay High Power Products

### True 2 Pin TO-220

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	METERS	INC	HES
STMBOL	MIN.	MAX.	MIN.	MAX.
A	4.32	4.57	0.170	0.180
b	0.71	0.91	0.028	0.036
b <sub>1</sub>	1.15	1.39	0.045	0.055
С	0.36	0.53	0.014	0.021
D	14.99	15.49	0.590	0.610
E	10.04	10.41	0.395	0.410
е	5.08	BSC	0.200 BSC	
F	1.22	1.37	0.048	0.054
H <sub>1</sub>	5.97	6.47	0.235	0.255
J <sub>1</sub>	2.54	2.79	0.100	0.110
L	13.47	13.97	0.530	0.550
L <sub>1</sub> <sup>(1)</sup>	3.31	3.81	0.130	0.150
ØР	3.79	3.88	0.149	0.153
Q	2.60	2.84	0.102	0.112

#### Notes

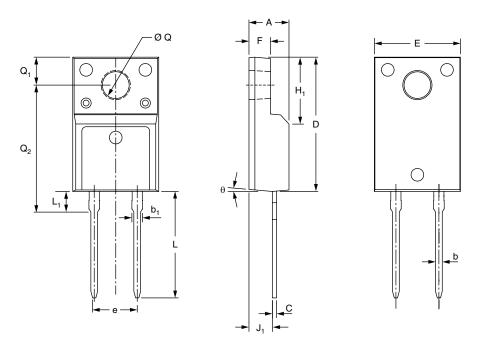
- (1) Lead dimension and finish uncontrolled in L<sub>1</sub>
- These dimensions are within allowable dimensions of JEDEC TO-220AB rev. J outline dated 3-24-87
- · Controling dimension: Inch



Vishay High Power Products

## True 2 Pin TO-220 FULL-PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	METERS	INCH	ES
SYMBOL	MIN.	MAX.	MIN.	MAX.
A	4.53	4.93	0.178	0.194
b	0.71	0.91	0.028	0.036
b <sub>1</sub>	1.15	1.39	0.045	0.055
С	0.36	0.53	0.014	0.021
D	15.67	16.07	0.617	0.633
E	9.96	10.36	0.392	0.408
е	5.08 typical		0.200 ty	pical
F	2.34	2.74	0.092	0.107
H <sub>1</sub>	6.50	6.90	0.256	0.272
J <sub>1</sub>	2.56	2.96	0.101	0.117
L	12.78	13.18	0.503	0.519
L <sub>1</sub>	2.23	2.63	0.088	0.104
ØQ	2.98	3.38	0.117	0.133
Q <sub>1</sub>	3.10	3.50	0.122	0.138
Q <sub>2</sub>	14.80	15.20	0.583	0.598
θ	0°	5°	0°	5°





Vishay

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